HA-5112/883

Dual, Low Noise, High Performance Uncompensated Operational Amplifier

October 2004

Features

- **This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.**
- **Low Input Noise Voltage Density at 1kHz. . . 6nV/$\sqrt{Hz}$(Max) 4.3nV/$\sqrt{Hz}$(Typ)**
- **High Slew Rate. . . . . .12V/μs (Min) 20V/μs (Typ)**
- **Wide Gain Bandwidth Product ($A_{VCL} \geq 10$) 54MHz**
- **Low Offset Voltage Drift . . . . . 3μV/^{o}C (Typ)**
- **High Open Loop Gain (Full Temp.). . . . . 100kV/V (Min) 250kV/V (Typ)**
- **High CMRR/PSRR (Full Temp.). . . . . .86dB (Min) 100dB (Typ)**
- **Low Offset Voltage Drift . . . . . 3μV/^{o}C (Typ)**
- **No Crossover Distortion**
- **Standard Dual Pinout**

Applications

- **High Quality Audio Preamplifiers**
- **High Q Active Filters**
- **Low Noise Function Generators**
- **Low Distortion Oscillators**
- **Low Noise Comparators**

Description

Low Noise and high performance are key words describing the dual, uncompensated HA-5112/883. This general purpose amplifier offers an array of dynamic specifications including 12V/μs slew rate (min), and 54MHz gain-bandwidth-product for $A_{VCL} \geq 10$. Complementing these outstanding parameters is a very low noise specification of 6nV/$\sqrt{Hz}$ at 1kHz (max).

Fabricated using the Intersil standard high frequency D.I. process, these operational amplifiers also offer excellent input specifications such as 2.5mV (max) offset voltage and 75nA (max) offset current. Complementing these specifications are 100dB (min) open loop gain and 55dB channel separation (min). The HA-5112/883 also consumes a very modest amount of supply power (180mW/package).

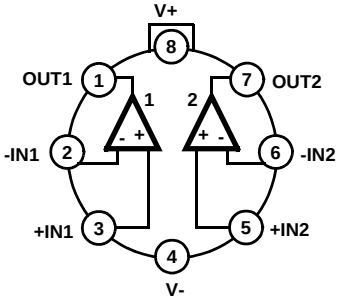
This impressive combination of features make this amplifier ideally suited for designs ranging from audio amplifiers and active filters to the most demanding signal conditioning and instrumentation circuits.

Part Number Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HA2-5112/883	-55^{o}C to +125^{o}C	8 Pin Can

Pinout

HA-5112/883
(METAL CAN)
TOP VIEW



Spec Number **511032-883**
FN3711.2

Absolute Maximum Ratings

Voltage between V+ and V- Terminals 40V
Differential Input Voltage 7V
Voltage at Either Input Terminal . . . . . V+ to V-
Peak Output Current . . . . . Indefinite
(One Amplifier Shorted to Ground)
Junction Temperature (T_J) . . . . . +175°C
Storage Temperature Range . . . . . -65°C to +150°C
ESD Rating . . . . . <2000V
Lead Temperature (Soldering 10s) . . . . . +300°C

Thermal Information

Thermal Resistance	θ_{JA}	θ_{JC}
Metal Can Package	160°C/W	70°C/W

Package Power Dissipation Limit at +75°C
Metal Can Package 645mW
Package Power Dissipation Derating Factor Above +75°C
Metal Can Package . . . . . 6.5mW/°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

1. θ_{JA} is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Operating Conditions

Operating Temperature Range . . . . . -55°C to +125°C
Operating Supply Voltage . . . . . ±5V to ±15V
$V_{INCM} \leq 1/2\ (V+ - V-)$
$R_L \geq 2k\Omega$

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm15V$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 500k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Input Offset Voltage	V_{IO}	$V_{CM} = 0V$	1	+25°C	-2.0	2.0	mV
			2, 3	+125°C, -55°C	-2.5	2.5	mV
Input Bias Current	$+I_B$	$V_{CM} = 0V$, $+R_S = 10k\Omega$, $-R_S = 100\Omega$	1	+25°C	-200	200	nA
			2, 3	+125°C, -55°C	-325	325	nA
	$-I_B$	$V_{CM} = 0V$, $+R_S = 100\Omega$, $-R_S = 10k\Omega$	1	+25°C	-200	200	nA
			2, 3	+125°C, -55°C	-325	325	nA
Input Offset Current	I_{IO}	$V_{CM} = 0V$, $+R_S = 10k\Omega$, $-R_S = 10k\Omega$	1	+25°C	-75	75	nA
			2, 3	+125°C, -55°C	-125	125	nA
Common Mode Range	+CMR	V+ = +3V, V- = -27V	1	+25°C	+12	-	V
			2, 3	+125°C, -55°C	+12	-	V
	-CMR	V+ = +27V, V- = -3V	1	+25°C	-	-12	V
			2, 3	+125°C, -55°C	-	-12	V
Large Signal Voltage Gain	$+A_{VOL}$	$V_{OUT} = 0V$ and +10V, $R_L = 2k\Omega$	4	+25°C	100	-	kV/V
			5, 6	+125°C, -55°C	100	-	kV/V
	$-A_{VOL}$	$V_{OUT} = 0V$ and -10V, $R_L = 2k\Omega$	4	+25°C	100	-	kV/V
			5, 6	+125°C, -55°C	100	-	kV/V
Common Mode Rejection Ratio	+CMRR	$\Delta V_{CM} = +5V$, V+ = +10V, V- = -20V, $V_{OUT} = -5V$	1	+25°C	86	-	dB
			2, 3	+125°C, -55°C	86	-	dB
	-CMRR	$\Delta V_{CM} = -5V$, V+ = +20V, V- = -10V, $V_{OUT} = +5V$	1	+25°C	86	-	dB
			2, 3	+125°C, -55°C	86	-	dB

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: V_{SUPPLY} = ±15V, R_{SOURCE} = 100Ω, R_{LOAD} = 500kΩ, V_{OUT} = 0V, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Voltage Swing	$+V_{OUT1}$	R_L = 2kΩ	1	+25°C	10	-	V
			2, 3	+125°C, -55°C	10	-	V
	$-V_{OUT1}$	R_L = 2kΩ	1	+25°C	-	-10	V
			2, 3	+125°C, -55°C	-	-10	V
	$+V_{OUT2}$	R_L = 10kΩ	1	+25°C	12	-	V
			2, 3	+125°C, -55°C	12	-	V
	$-V_{OUT2}$	R_L = 10kΩ	1	+25°C	-	-12	V
			2, 3	+125°C, -55°C	-	-12	V
Output Current	$+I_{OUT}$	V_{OUT} = -5V	1	+25°C	10	-	mA
			2, 3	+125°C, -55°C	10	-	mA
	$-I_{OUT}$	V_{OUT} = +5V	1	+25°C	-	-10	mA
			2, 3	+125°C, -55°C	-	-10	mA
Quiescent Power Supply Current	$+I_{CC}$	V_{OUT} = 0V, I_{OUT} = 0mA	1	+25°C	-	5	mA
			2, 3	+125°C, -55°C	-	6	mA
	$-I_{CC}$	V_{OUT} = 0V, I_{OUT} = 0mA	1	+25°C	-5	-	mA
			2, 3	+125°C, -55°C	-6	-	mA
Power Supply Rejection Ratio	+PSRR	ΔV_{SUP} = 10V, V+ = +10V, V- = -15V V+ = +20V, V- = -15V	1	+25°C	86	-	dB
			2, 3	+125°C, -55°C	86	-	dB
	-PSRR	ΔV_{SUP} = 10V, V+ = +15V, V- = -10V V+ = +15V, V- = -20V	1	+25°C	86	-	dB
			2, 3	+125°C, -55°C	86	-	dB

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 2 Intentionally Left Blank. See AC Parameters in Table 3

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: V_{SUPPLY} = ±15V, R_{LOAD} = 2kΩ, C_{LOAD} = 50pF, A_{VCL} = 10V/V, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Differential Input Resistance	R_{IN}	V_{CM} = 0V	1	+25°C	250	-	kΩ
Input Noise Voltage	E_N	R_S = 20Ω, f_O = 1000Hz	1	+25°C	-	6	$nV/\sqrt{Hz}$
Input Noise Current	I_N	R_S = 2MΩ, f_O = 1000Hz	1	+25°C	-	3	$pA/\sqrt{Hz}$
Gain Bandwidth Product	GBWP	V_O = 200mV, f_O = 50kHz	1	+25°C	40	-	MHz
		V_O = 200mV, f_O = 1MHz	1	+25°C	54	-	MHz

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Characterized at: V_{SUPPLY} = ±15V, R_{LOAD} = 2kΩ, C_{LOAD} = 50pF, A_{VCL} = 10V/V, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Slew Rate	+SR	V_{OUT} = -5V to +5V	1	+25°C	12	-	V/µs
	-SR	V_{OUT} = +5V to -5V	1	+25°C	12	-	V/µs
Full Power Bandwidth	FPBW	V_{PEAK} = 10V	1, 2	+25°C	191	-	kHz
Minimum Closed Loop Stable Gain	CLSG	R_L = 2kΩ, C_L = 50pF	1	-55°C to +125°C	10	-	V/V
Rise and Fall Time	t_R	V_{OUT} = 0V to +200mV	1, 4	+25°C	-	100	ns
	t_F	V_{OUT} = 0V to -200mV	1, 4	+25°C	-	100	ns
Overshoot	+OS	V_{OUT} = 0V to +200mV	1	+25°C	-	40	%
	-OS	V_{OUT} = OV to -200mV	1	+25°C	-	40	%
Output Resistance	R_{OUT}	Open Loop	1	+25°C	-	232	Ω
Quiescent Power Consumption	PC	V_{OUT} = 0V, I_{OUT} = 0mA	1, 3	-55°C to +125°C	-	180	mW
Channel Separation	CS	R_S = 1kΩ, A_{VCL} = 100V/V, V_{IN} = 100mV_{PEAK} at 10kHz, Referred to Input	1	+25°C	55	-	dB

NOTES:

1. Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.
2. Full Power Bandwidth guarantee based on Slew Rate measurement using FPBW = Slew Rate/($2\pi V_{PEAK}$).
3. Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on outputs.).
4. Measured between 10% and 90% points.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4, 5, 6
Group A Test Requirements	1, 2, 3, 4, 5, 6
Groups C and D Endpoints	1

NOTE:

1. PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:
98.4 x 67.3 x 19 mils ± 1 mils
2500 x 1710 x 483µm ± 25.4µm

METALLIZATION:
Type: Al, 1% Cu
Thickness: 16kÅ ± 2kÅ

GLASSIVATION:
Type: Nitride (Si3N4) over Silox (SiO2, 5% Phos.)
Silox Thickness: 12kÅ ± 2kÅ
Nitride Thickness: 3.5kÅ ± 1.5kÅ

WORST CASE CURRENT DENSITY:
1.43 x 10^5A/cm^2 at 10mA

SUBSTRATE POTENTIAL (Powered Up):
Unbiased

TRANSISTOR COUNT: 93

PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout

HA-5112/883